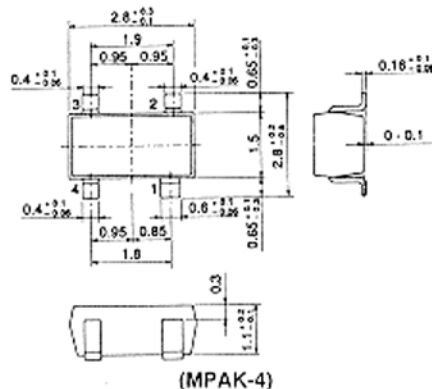


3SK154

SILICON N-CHANNEL DUAL GATE MOS FET

VHF AMPLIFIER

VHF TV TUNER RF AMPLIFIER

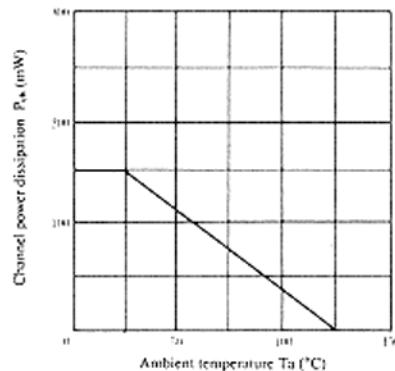


1. Source
 2. Gate 1
 3. Gate 2
 4. Drain
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	3SK154	Unit
Drain to source voltage	V_{DSX}	15	V
Gate 1 to source voltage	V_{G1S}	±8	V
Gate 2 to source voltage	V_{G2S}	±8	V
Drain current	I_D	35	mA
Channel power dissipation	P_{ch}	150	mW
Channel temperature	T_{ch}	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

MAXIMUM CHANNEL POWER DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain to source breakdown voltage	$V_{(BR)DSX}$	$V_{G1S} = V_{G2S} = -8V, I_D = 200\mu A$	15	—	—	V
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	$I_{G1} = \pm 10\mu A, V_{G2S} = V_{DS} = 0$	±8	—	±20	V
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	$I_{G2} = \pm 10\mu A, V_{G1S} = V_{DS} = 0$	±8	—	±20	V
Gate 1 cutoff current	I_{G1SS}	$V_{G1S} = \pm 8V, V_{G2S} = V_{DS} = 0$	—	—	±100	nA
Gate 2 cutoff current	I_{G2SS}	$V_{G2S} = \pm 8V, V_{G1S} = V_{DS} = 0$	—	—	±100	nA
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	$V_{DS} = 10V, V_{G2S} = 3V, I_D = 100\mu A$	—	—	-2	V
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	$V_{DS} = 10V, V_{G1S} = 3V, I_D = 100\mu A$	—	—	-2	V
Drain current	I_{DSS}	$V_{DS} = 6V, V_{G2S} = 3V, V_{G1S} = 0$	—	—	30	mA
Forward transfer admittance	$ y_{fs} $	$V_{DS} = 6V, V_{G2S} = 3V, I_D = 10mA, f = 1kHz$	15	—	—	mS
Input capacitance	C_{iss}	$V_{DS} = 6V, V_{G2S} = 3V, I_D = 10mA, f = 1MHz$	—	4.5	—	pF
Output capacitance	C_{oss}		—	3	—	pF
Reverse transfer capacitance	C_{rss}		—	0.03	—	pF
Power gain	PG	$V_{DS} = 6V, V_{G2S} = 3V, I_D = 10mA, f = 200MHz$	22	—	—	dB
Noise figure	NF		—	—	3	dB

* Marking is [1Z-].

■ See characteristic curves of 3SK96.